	Type	Ref #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	S1	55939	etch$3 and (transistor or MOS or memory or bitline or dram or "dynamic random access memory" or capacitor) and ((contact adj (hole or open$3)) or sac or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 17:21			
2	BRS	S2	43318	etch$3 and (transistor or MOS or memory or bitline or dram or "dynamic random access memory" or capacitor) and gate and ((contact adj (hole or open$3)) or sac or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 17:21			
3	BRS	S3	9402	etch$3 same (transistor or MOS or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 17:24			
4	BRS	S4	7410	S3 and @pd<="20040220"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 17:24			
5	BRS	S5	8862	etch$3 same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 17:25			
6	BRS	S6	6970	S5 and @pd<="20040220"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 17:26			
7	BRS	S7	1704	(etch$3 same (plasma or gas or dry)) same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/18 19:12			

	Type	Ref #	Hits	Search Text	DBs	Time Stamp	C mments	Err r Definiti n	Errors
8	BRS	S8	1292	S7 and @pd<="20040220"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:14			
9	BRS	S9	5678	S6 not S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 18:19			
10	BRS	S10	37	(etch$3 same (plasma or gas or dry)) same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) same capp$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:16			
11	BRS	S11	28	S10 and @pd<="20040220"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:17			
12	BRS	S12	8862	etch$3 same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:17			
13	BRS	S13	224	etch$3 same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) same capp$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:17			
14	BRS	S14	166	S13 and @pd<="20040220"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:29			

	Type	Ref #	Hits	Search Text	DBs	Time Stamp	Comments	Err r Definition	Err rs
15	BRS	S15	131	CHEN-YI-NAN.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:32			
16	BRS	S16	39	HUANG-TSE-YAO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:34			
17	BRS	S17	32	MAO-HUI-MIN.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2005/10/ 18 19:34			